

CS 95-013

LOW-PROFILE-SHALLOW TRENCH DOUBLE POLYSILICON CAPACITOR

ABSTRACT OF THE DISCLOSURE

A double layer planar polysilicon capacitor for use within integrated circuits and a method by which that planar polysilicon capacitor is formed. Formed within a semiconductor substrate is a deep trench which is filled with a dielectric material. Formed within the dielectric material within the deep trench is a shallow trench which has a first polysilicon capacitor plate formed therein. The upper surface of the first polysilicon capacitor plate is substantially planar with the semiconductor substrate. Formed upon the first polysilicon capacitor plate is a polysilicon capacitor dielectric layer. Formed upon the polysilicon capacitor dielectric layer is a second polysilicon capacitor plate.

(FIGURE 2 IS SUGGESTED FOR PUBLICATION)